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(54) **SEMICONDUCTOR DEVICE**

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(57) **ABSTRACT**

A semiconductor device includes a gate structure on a substrate and an epitaxial layer adjacent to the gate structure, in which the epitaxial layer includes a first buffer layer, a second buffer layer on the first buffer layer, a bulk layer on the second buffer layer, a first cap layer on the bulk layer, and a second cap layer on the first cap layer. Preferably, the bottom surface of the first buffer layer includes a linear surface, a bottom surface of the second buffer layer includes a curve, and the second buffer layer includes a linear sidewall.